

Francis Maury

List of Publications by Year in descending order

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126
papers

2,069
citations

236925

25
h-index

315739

38
g-index

127
all docs

127
docs citations

127
times ranked

1836
citing authors

#	ARTICLE	IF	CITATIONS
1	Scanning Strategy Investigation for Direct Powder Bed Selective Laser Processing of Silicon Carbide Ceramic. <i>Applied Sciences (Switzerland)</i> , 2022, 12, 788.	2.5	9
2	Process parameters investigation for direct powder bed selective laser processing of silicon carbide parts. <i>Progress in Additive Manufacturing</i> , 2022, 7, 1307-1322.	4.8	4
3	Two new inorganic-organic hybrid materials based on U^{2+} - and U^{3+} -octamolybdate clusters: Synthesis, structure determination and solid-state photochromic properties. <i>Polyhedron</i> , 2021, 194, 114919.	2.2	3
4	A review of additive manufacturing of ceramics by powder bed selective laser processing (sintering / Overlock 10 Tf. 2021, 5, 100073.	2.0	67
5	Experimental and numerical study for direct powder bed selective laser processing (sintering/melting) of silicon carbide ceramic. <i>Materials Research Express</i> , 2021, 8, 045603.	1.6	13
6	Low temperature Direct Liquid Injection MOCVD of amorphous Cr_x coatings in large-scale reactors: An original route to nanostructured multilayer coatings. <i>Surface and Coatings Technology</i> , 2021, 416, 127174.	4.8	2
7	Densification of surface-modified silicon carbide powder by spark-plasma-sintering. <i>Journal of the European Ceramic Society</i> , 2021, 41, 7543-7551.	5.7	12
8	A new good thermal stability hybrid material based on heptamolybdate cluster: Synthesis and structural characterization. <i>Chemical Data Collections</i> , 2020, 30, 100576.	2.3	1
9	One pot-synthesis of the fourth category of dinuclear molybdenum(VI) oxalate series: Structure and study of thermal and redox properties. <i>Inorganica Chimica Acta</i> , 2019, 491, 84-92.	2.4	5
10	Chromium Carbide Growth by Direct Liquid Injection Chemical Vapor Deposition in Long and Narrow Tubes, Experiments, Modeling and Simulation. <i>Coatings</i> , 2018, 8, 220.	2.6	18
11	Non-hydrothermal synthesis and structure determination of two new U^{2+} -octamolybdate (VI) stabilized with dialkylammonium counterions. <i>Journal of Molecular Structure</i> , 2018, 1170, 44-50.	3.6	8
12	Visible Thermochromism in Vanadium Pentoxide Coatings. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 21447-21456.	8.0	45
13	In Recognition of Professor Hitchman: Advances in Chemical Vapor Deposition. <i>Advanced Materials Interfaces</i> , 2017, 4, 1700984.	3.7	0
14	Optical and morphological properties of thermochromic V_2O_5 coatings. <i>Data in Brief</i> , 2017, 14, 348-353.	1.0	2
15	Tunable thermochromic properties of V_2O_5 coatings. <i>Materials Today Physics</i> , 2017, 2, 1-5.	6.0	20
16	Evidence for a Cr metastable phase as a tracer in DLI-MOCVD chromium hard coatings usable in high temperature environment. <i>Applied Surface Science</i> , 2017, 422, 198-206.	6.1	14
17	Light modulation in phase change disordered metamaterial - A smart cermet concept. <i>Materials Today Physics</i> , 2017, 3, 41-47.	6.0	6
18	Antibacterial properties of TiO_2/Cu composite thin films grown by a one step DLICVD process. <i>Surface and Coatings Technology</i> , 2014, 242, 187-194.	4.8	24

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19	Comprehensive physicochemical study of dioctahedral palygorskite-rich clay from Marrakech High Atlas (Morocco). <i>Physics and Chemistry of Minerals</i> , 2013, 40, 411-424.	0.8	41
20	Evidences for liquid encapsulation in PMMA ultra-thin film grown by liquid injection Photo-CVD. <i>Progress in Organic Coatings</i> , 2013, 76, 1846-1850.	3.9	3
21	Physicochemical Study of Photocatalytic Activity of TiO ₂ Supported Palygorskite Clay Mineral. <i>International Journal of Photoenergy</i> , 2013, 2013, 1-6.	2.5	23
22	Thermally Induced Release of Internal Liquid Phase Encapsulated in a Polymer Membrane Grown by Photoactivated DLICVD. <i>Chemical Vapor Deposition</i> , 2012, 18, 274-281.	1.3	2
23	Embedded layer of Ag nanoparticles prepared by a combined PECVD/PVD process producing SiO _x CyAg nanocomposite thin films. <i>Nanotechnology</i> , 2012, 23, 015603.	2.6	9
24	Synthesis, characterization and photocatalytic activity of TiO ₂ supported natural palygorskite microfibers. <i>Applied Clay Science</i> , 2011, 52, 301-311.	5.2	107
25	CVD Elaboration of Nanostructured TiO ₂ Ag Thin Films with Efficient Antibacterial Properties. <i>Chemical Vapor Deposition</i> , 2010, 16, 35-41.	1.3	45
26	Vapor phase surface functionalization under ultra violet activation of parylene thin films grown by chemical vapor deposition. <i>Thin Solid Films</i> , 2010, 518, 1675-1681.	1.8	23
27	TiO _x Ny coatings grown by atmospheric pressure metal organic chemical vapor deposition. <i>Surface and Coatings Technology</i> , 2010, 205, 1287-1293.	4.8	33
28	Correlation between eletrokinetic mobility and ionic dyes adsorption of Moroccan stevensite. <i>Applied Clay Science</i> , 2010, 48, 527-530.	5.2	28
29	Chemical vapor deposition and characterization of nitrogen doped TiO ₂ thin films on glass substrates. <i>Thin Solid Films</i> , 2009, 518, 1299-1303.	1.8	33
30	Multilayer chromium based coatings grown by atmospheric pressure direct liquid injection CVD. <i>Surface and Coatings Technology</i> , 2009, 204, 983-987.	4.8	20
31	DLI-CVD of TiO ₂ Cu antibacterial thin films: Growth and characterization. <i>Surface and Coatings Technology</i> , 2009, 204, 887-892.	4.8	56
32	Microfibrous TiO ₂ supported photocatalysts prepared by metal-organic chemical vapor infiltration for indoor air and waste water purification. <i>Applied Catalysis B: Environmental</i> , 2009, 91, 225-233.	20.2	43
33	Chemical Vapor Deposition of TiO ₂ for Photocatalytic Applications and Biocidal Surfaces. <i>Key Engineering Materials</i> , 2009, 415, 1-4.	0.4	11
34	Diagnostic in CVD processes by IR pyrometry. <i>Chemical Engineering and Processing: Process Intensification</i> , 2008, 47, 383-389.	3.6	1
35	In situ IR pyrometric analysis during thermal treatment in air of TiO _x Ny coatings. <i>Surface and Coatings Technology</i> , 2008, 202, 2423-2427.	4.8	3
36	Thermodynamic simulation of atmospheric DLI-CVD processes for the growth of chromium-based hard coatings using bis(benzene)chromium as molecular source. <i>Surface and Coatings Technology</i> , 2008, 203, 516-520.	4.8	10

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37	Elucidating the crystal-chemistry of Jbel Rhassoul stevensite (Morocco) by advanced analytical techniques. <i>Clay Minerals</i> , 2008, 43, 393-403.	0.6	43
38	Optimization of the Vaporization of Liquid and Solid CVD Precursors: Experimental and Modeling Approaches. <i>Chemical Vapor Deposition</i> , 2007, 13, 638-643.	1.3	16
39	Growth of TiO ₂ thin films by AP-MOCVD on stainless steel substrates for photocatalytic applications. <i>Surface and Coatings Technology</i> , 2007, 201, 9304-9308.	4.8	42
40	N-doped TiO ₂ coatings grown by atmospheric pressure MOCVD for visible light-induced photocatalytic activity. <i>Surface and Coatings Technology</i> , 2007, 201, 9349-9353.	4.8	42
41	Chemical vapor infiltration of photocatalytically active TiO ₂ thin films on glass microfibers. <i>Surface and Coatings Technology</i> , 2007, 201, 9354-9358.	4.8	10
42	Pyrosol deposition of anatase TiO ₂ thin films starting from Ti(OiPr) ₄ /acetylacetonone solutions. <i>Thin Solid Films</i> , 2007, 515, 7732-7739.	1.8	20
43	Diagnostic in TCOs CVD processes by IR pyrometry. <i>Thin Solid Films</i> , 2007, 515, 8619-8623.	1.8	7
44	SnO ₂ coated Ni particles prepared by fluidized bed chemical vapor deposition. <i>Surface and Coatings Technology</i> , 2006, 200, 6733-6739.	4.8	12
45	Nanocrystalline chromium-based coatings deposited by DLI-MOCVD under atmospheric pressure from Cr(CO) ₆ . <i>Surface and Coatings Technology</i> , 2006, 200, 6267-6271.	4.8	12
46	Iron Thin Films from Fe(CO) ₅ and FeCp ₂ •H ₂ O under Atmospheric Pressure. <i>Journal of the Electrochemical Society</i> , 2006, 153, G1025.	2.9	10
47	MOCVD of hard metallurgical coatings: Examples in the Cr-C-N system. <i>Electrochimica Acta</i> , 2005, 50, 4525-4530.	5.2	7
48	Chromium-based coatings by atmospheric chemical vapor deposition at low temperature from Cr(CO) ₆ . <i>Surface and Coatings Technology</i> , 2005, 200, 1407-1412.	4.8	11
49	MOCVD of Cr ₃ (C,N) ₂ and CrSi _x C _y Films. <i>Journal of the Electrochemical Society</i> , 2005, 152, G651.	2.9	1
50	MOCVD of Cr ₃ (C,N) ₂ and CrSi _x C _y Films. <i>Journal of the Electrochemical Society</i> , 2005, 152, G907.	2.9	2
51	Atmospheric pressure MOCVD of TiO ₂ thin films using various reactive gas mixtures. <i>Surface and Coatings Technology</i> , 2004, 188-189, 255-259.	4.8	49
52	In-Situ Optical Pyrometry in the CVD of Metallic Thin Films for Real Time Control of the Growth. <i>Chemical Vapor Deposition</i> , 2003, 9, 34-39.	1.3	5
53	Iridium coatings grown by metal-organic chemical vapor deposition in a hot-wall CVD reactor. <i>Surface and Coatings Technology</i> , 2003, 163-164, 208-213.	4.8	41
54	Chemical Vapor Deposition of Cr-Based Thin Films as Diffusion Barriers in Copper Metallization. <i>Materials Science Forum</i> , 2003, 426-432, 3439-3444.	0.3	0

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55	Study of the properties of in situ Pt-doped SnO ₂ thin films prepared by metal-organic chemical vapour deposition. <i>Annales De Chimie: Science Des Materiaux</i> , 2002, 27, 61-68.	0.4	0
56	A miniaturised silicon based enzymatic biosensor: towards a generic structure and technology for multi-analytes assays. <i>Sensors and Actuators B: Chemical</i> , 2002, 82, 227-232.	7.8	20
57	Chemical vapor deposition of SnO ₂ coatings on Ti plates for the preparation of electrocatalytic anodes. <i>Surface and Coatings Technology</i> , 2002, 151-152, 9-13.	4.8	41
58	Real time monitoring of the growth of metallic thin films by in situ pyrometry. <i>European Physical Journal Special Topics</i> , 2002, 12, 9-8.	0.2	56
59	Photo-MOCVD of copper thin films using Cu(II) and Cu(I) precursors for low-temperature metallization. <i>Advanced Materials for Optics and Electronics</i> , 2000, 10, 123-133.	0.4	9
60	Photo-assisted MOCVD of copper using Cu(hfa)(COD) as precursor. <i>Applied Surface Science</i> , 2000, 168, 57-60.	6.1	8
61	Al ₂ O ₃ coatings on stainless steel from Al metal-organic chemical vapor deposition and thermal treatments. <i>Surface and Coatings Technology</i> , 2000, 125, 419-423.	4.8	32
62	Single-phased hard coatings of the metastable Cr ₃ (CO _{0.8} N _{0.2}) ₂ ternary phase grown by low pressure MOCVD. <i>Surface and Coatings Technology</i> , 2000, 133-134, 198-202.	4.8	5
63	Chemical vapor deposition of tin oxide from SnEt ₄ . <i>European Physical Journal Special Topics</i> , 1999, 09, Pr8-651-Pr8-657.	0.2	3
64	Low Temperature Metallorganic Chemical Vapor Deposition Routes to Chromium Metal Thin Films Using Bis(benzene)chromium. <i>Journal of the Electrochemical Society</i> , 1999, 146, 3716-3723.	2.9	12
65	Threshold photoemission analysis of the surface reactions of triethylgallium and trimethylgallium on GaAs(100): A promising technique for kinetics studies. <i>Applied Physics Letters</i> , 1999, 74, 266-268.	3.3	5
66	Photo-MOCVD of Cu thin films using Cu(hfa)(MHY) as precursor. <i>European Physical Journal Special Topics</i> , 1999, 09, Pr8-791-Pr8-798.	0.2	1
67	MOCVD and properties of in situ doped Pt-SnO ₂ thin films. <i>European Physical Journal Special Topics</i> , 1999, 09, Pr8-643-Pr8-650.	0.2	0
68	Metalorganic chemical vapor deposition of SnO thin films using tetraethyltin: Growth and characterization. <i>Annales De Chimie: Science Des Materiaux</i> , 1998, 23, 355-358.	0.4	4
69	Chemical vapor deposition of Ge thin films using GeEt ₄ : study of the reaction mechanisms. <i>Annales De Chimie: Science Des Materiaux</i> , 1998, 23, 381-384.	0.4	3
70	Précurseurs métallorganiques pour le dépôt chimique à partir d'une phase gazeuse de revêtements dans le système Ti-V-C-N. <i>Annales De Chimie: Science Des Materiaux</i> , 1998, 23, 637-653.	0.4	1
71	Mécanisme de décomposition des composés M(NEt ₃) (M = V, Cr) lors de leur utilisation comme mono-source pour la croissance de films M-C-N par MOCVD. <i>Annales De Chimie: Science Des Materiaux</i> , 1998, 23, 667-679.	0.4	2
72	Dépôt de Cr à basse température par MOCVD: inhibition de l'incorporation du carbone. <i>Annales De Chimie: Science Des Materiaux</i> , 1998, 23, 681-693.	0.4	0

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73	Départ chimique en phase vapeur à basse température de revêtements dans le système V-C-N à partir de bis(arene)vanadium. <i>Annales De Chimie: Science Des Matériaux</i> , 1998, 23, 695-706.	0.4	3
74	Prétraitements de nitruration compatibles avec les procédés MOCVD et PACVD: Influence sur l'adhérence de revêtements céramiques sur ACIER. <i>Annales De Chimie: Science Des Matériaux</i> , 1998, 23, 707-720.	0.4	2
75	Low-temperature MOCVD of chromium carbonitride coatings from tetrakis(diethylamido)chromium and pyrolysis mechanism of this single-source precursor. <i>Applied Organometallic Chemistry</i> , 1998, 12, 189-199.	3.5	6
76	A Thermodynamic Approach to the CVD of Chromium and of Chromium Carbides Starting from Cr(C ₆ H ₆) ₂ . <i>Chemical Vapor Deposition</i> , 1998, 4, 69-76.	1.3	12
77	Driving Force for Free-Carbon Incorporation in Chromium Carbide Films Processed by MOCVD. <i>Chemical Vapor Deposition</i> , 1998, 4, 96-99.	1.3	1
78	Gas and plasma nitriding pretreatments of steel substrates before CVD growth of hard refractory coatings. <i>Thin Solid Films</i> , 1998, 315, 179-185.	1.8	12
79	Making of specific electrodes by CVD. <i>Surface and Coatings Technology</i> , 1998, 100-101, 169-172.	4.8	8
80	Low-temperature MOCVD of V-C-N coatings using bis(arene)vanadium as precursors. <i>Surface and Coatings Technology</i> , 1998, 108-109, 200-205.	4.8	10
81	Thermal decomposition mechanisms of tetraethylgermane in metal-organic chemical vapor deposition. <i>Journal of Analytical and Applied Pyrolysis</i> , 1998, 44, 153-165.	5.5	13
82	A Thermodynamic Approach to the CVD of Chromium and of Chromium Carbides Starting from Cr(C ₆ H ₆) ₂ . <i>Chemical Vapor Deposition</i> , 1998, 04, 69-76.	1.3	20
83	Driving Force for Free-Carbon Incorporation in Chromium Carbide Films Processed by MOCVD. <i>Chemical Vapor Deposition</i> , 1998, 04, 96-99.	1.3	2
84	Chemical beam epitaxy of CoGa on GaAs using GaEt ₃ and CpCo(CO) ₂ as dual organometallic sources. <i>Microelectronic Engineering</i> , 1997, 37-38, 165-171.	2.4	2
85	MOCVD Route to Chromium Carbonitride Thin Films Using Cr(NEt ₂) ₄ as Single-Source Precursor: Growth and Mechanism. <i>Chemical Vapor Deposition</i> , 1997, 3, 137-143.	1.3	8
86	Thermal decomposition of V(NEt ₂) ₄ in a MOCVD reactor: a low-temperature route to vanadium carbonitride coatings. <i>Journal of Materials Chemistry</i> , 1996, 6, 1501.	6.7	12
87	Trends in precursor selection for MOCVD. <i>Chemical Vapor Deposition</i> , 1996, 2, 113-116.	1.3	49
88	Selection of metalorganic precursors for MOCVD of metallurgical coatings: application to Cr-based coatings. <i>Surface and Coatings Technology</i> , 1996, 86-87, 316-324.	4.8	22
89	GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic. <i>Applied Surface Science</i> , 1995, 86, 447-452.	6.1	8
90	Mass Spectrometric Study of the Gas Phase During Chemical Vapor Deposition of Pyrolytic Carbon. <i>European Physical Journal Special Topics</i> , 1995, 05, C5-89-C5-96.	0.2	2

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91	Control of the uniformity of thickness of Ni thin films deposited by low pressure chemical vapor deposition. <i>Surface and Coatings Technology</i> , 1994, 64, 21-27.	4.8	13
92	Investigation of [(py) (Et) Co(dmg \hat{A} GaEt ₂) ₂] and [Ni(dmg \hat{A} GaEt ₂) ₂] (py = pyridine; dmg =) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 70 structure of [(py)(Et)Co(dmg \hat{A} GaEt ₂)(dmgH)]. <i>Journal of Organometallic Chemistry</i> , 1994, 472, 317-328.	1.8	30
93	Co-pyrolysis of hydrocarbons and SiEt ₄ for the synthesis of graduated SixC1 \hat{A} ceramic thin films by chemical vapour deposition. <i>Journal of Materials Chemistry</i> , 1994, 4, 695-701.	6.7	10
94	Study of CoGa deposition from the single source precursor (CO) ₄ CoGaCl ₂ (THF). <i>Journal of Organometallic Chemistry</i> , 1993, 449, 159-165.	1.8	25
95	Epitaxial growth of cobalt-gallium on gallium arsenide by organometallic chemical vapor deposition. <i>Chemistry of Materials</i> , 1993, 5, 84-89.	6.7	22
96	Organometallic vapor phase epitaxy of CoGa on (100)GaAs. <i>Applied Physics Letters</i> , 1992, 61, 1075-1077.	3.3	7
97	Chemical vapour infiltration of SixC1 \hat{A} films for the preparation of composite materials using both organosilicon and hydrocarbon precursors. <i>Thin Solid Films</i> , 1992, 209, 52-58.	1.8	4
98	Evaluation of tetra-alkylchromium precursors for organometallic chemical vapour deposition I. films grown using Cr[CH ₂ C(CH ₃) ₃] ₄ . <i>Thin Solid Films</i> , 1992, 207, 82-89.	1.8	25
99	Evaluation of tetra-alkylchromium precursors for organometallic chemical vapor deposition II: Unusual low temperature chromium carbide deposition from Cr[C(CH ₃) ₃] ₄ . <i>Thin Solid Films</i> , 1992, 219, 24-29.	1.8	14
100	Organochromium precursors for low-temperature OMCVD of chromium-based coatings. <i>Applied Organometallic Chemistry</i> , 1992, 6, 619-626.	3.5	8
101	Assessment of tetra-alkylchromium compounds for low temperature organo-metallic chemical vapour deposition of Cr-based coatings. <i>Surface and Coatings Technology</i> , 1992, 54-55, 204-210.	4.8	3
102	Chemical and structural characterizations of chemical vapour deposited SixC1 \hat{A} films. <i>Materials Letters</i> , 1991, 11, 257-260.	2.6	7
103	Characterization of chromium nitride and carbonitride coatings deposited at low temperature by organometallic chemical vapour deposition. <i>Surface and Coatings Technology</i> , 1991, 46, 275-288.	4.8	49
104	Residual stresses analyses of metallo-organic chemically vapour-deposited Cr ₇ C ₃ coatings on SAE 4135 steel substrates. <i>Surface and Coatings Technology</i> , 1991, 45, 185-192.	4.8	6
105	Organometallic molecular precursors for low-temperature MOCVD of III-V semiconductors. <i>Advanced Materials</i> , 1991, 3, 542-548.	21.0	39
106	Influence of organochromium precursor chemistry on the microstructure of MOCVD chromium carbide coatings. <i>Surface and Coatings Technology</i> , 1990, 43-44, 185-198.	4.8	25
107	Structural characterization of chromium carbide coatings deposited at low temperature by low pressure chemical vapour decomposition using dicumene chromium. <i>Surface and Coatings Technology</i> , 1990, 41, 51-61.	4.8	24
108	Organo-metallic chemical vapour deposition of silicon-rich amorphous SixC1 \hat{A} refractory layers using SiEt ₄ as a single source. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 1989, 109, 69-75.	5.6	12

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109	Pyrolysis of various organosilazanes used as single precursor of SiN _x Cy:H films OMCVD process. Journal of Analytical and Applied Pyrolysis, 1989, 17, 67-81.	5.5	4
110	EVIDENCE FOR FREE CARBON IN AMORPHOUS OMCVD SILICON-RICH Si _x C _{1-x} COATINGS. Journal De Physique Colloque, 1989, 50, C5-765-C5-772.	0.2	0
111	Mass spectrometric study of the pyrolysis of organometallic precursors usable in GaAs vapor phase epitaxy. Journal of Crystal Growth, 1988, 91, 97-104.	1.5	9
112	Mass spectrometric study of the pyrolysis of organometallic precursors usable in GaAs vapor phase epitaxy. Journal of Crystal Growth, 1988, 91, 105-110.	1.5	12
113	Raman scattering analysis of disorder in heterogeneous (GaAs) _{1-x} (SiC ₂ :H) _x films grown by metal-organic chemical vapour deposition. Thin Solid Films, 1987, 155, 331-342.	1.8	9
114	A.c. properties of polycrystalline GaAs and (GaAs) _{1-x} (SiC ₂ :H) _x grown by metal-organic chemical vapour deposition. Thin Solid Films, 1987, 146, 241-254.	1.8	1
115	Structural characterizations of MOCVD (GaAs) _{1-x} (SiC ₂ H) _x films: Evidence for a multiphase structure. Materials Letters, 1986, 4, 249-255.	2.6	2
116	Optical and electrical properties of the disordered composite semiconductor (GaAs) _{1-x} (SiC ₂ :H) _x , grown by metal-organic chemical vapour deposition. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1986, 53, 445-457.	0.6	3
117	Some investigations on the chemisorption and thermal heterogeneous decomposition of the MOCVD adduct ClMe ₂ GaAsEt ₃ . Journal of Crystal Growth, 1986, 78, 185-188.	1.5	7
118	Metal-organic chemical vapour codeposition of GaAs and SixCl _{1-x} groups: Growth of a new amorphous semiconductor. Thin Solid Films, 1984, 117, 299-309.	1.8	6
119	MOVPE of GaAs from the new adducts [CIR ₂ Ga-AsEt ₂] ₂ CH ₂ (R = Me, Et) and (C ₆ F ₅) ₃ n MenGa-AsEt ₃ (n) Tj ETQq1 1,0.784314	1.5	25
120	Synthesis and characterization of diethylphosphino Ga(III) and In(III) complexes with covalent metal-phosphorus bonds. Polyhedron, 1984, 3, 581-584.	2.2	40
121	Croissance Épitaxiale de GaAs _{1-x} P _x (0 < x < 0.6) par OM-CVD À partir du complexe ClEt ₂ Ga-AsEt ₃ et de la diethyl phosphine: une source de phosphore originale HPEt ₂ . Journal of Crystal Growth, 1983, 62, 568-576.	1.5	15
122	Various chemical mechanisms for the crystal growth of III-V semiconductors using coordination compounds as starting material in the MOCVD process. Journal of Crystal Growth, 1981, 55, 135-144.	1.5	59
123	Synthesis and crystal structures of lithium and of sodium bis(dithioxalato)nickelate(II). Comparison with the potassium derivatives. Inorganica Chimica Acta, 1980, 41, 185-194.	2.4	10
124	Orbital interactions in a strongly antiferromagnetically coupled copper(II) linear chain: CuSe ₂ O ₅ . Solid State Communications, 1980, 34, 971-975.	1.9	17
125	Crystal structure and magnetism of sodium bis(oxalato)cuprate(II)dihydrate, Na ₂ Cu(C ₂ O ₄) ₂ .2H ₂ O. A deductive proposal for the structure of copper oxalate, CuC ₂ O ₄ .xH ₂ O (O .ltoreq. .times. .ltoreq. 1). Inorganic Chemistry, 1980, 19, 2074-2078.	4.0	55
126	Comparative Study of Antibacterial Efficiency of M-TiO ₂ (M = Ag, Cu) Thin Films Grown by CVD. Key Engineering Materials, 0, 617, 127-130.	0.4	4